FAIRCHILD SEMICONDUCTOR®

September 2009

TIL111M, TIL117M, MOC8100M
General Purpose 6-Pin Phototransistor Optocouplers

Features

- UL recognized (File # E90700)
- VDE recognized (File #102497 for white package)
  - Add option V (e.g., TIL111VM)

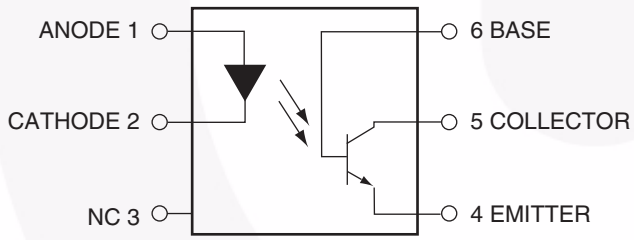
Applications

- Power supply regulators
- Digital logic inputs
- Microprocessor inputs
- Appliance sensor systems
- Industrial controls

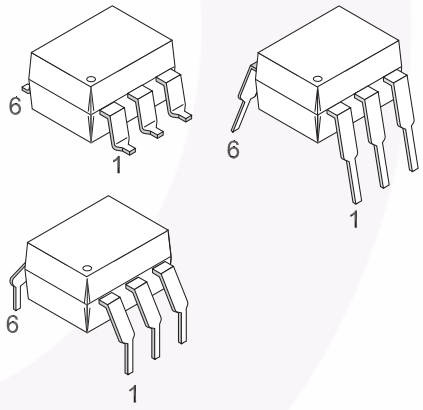
General Description

The MOC8100M, TIL111M and TIL117M optocouplers consist of a gallium arsenide infrared emitting diode driving a silicon phototransistor in a 6-pin dual in-line package.

Schematic



Package Outlines



Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Parameter	Device	Value	Units
TOTAL DEVICE				
T_{STG}	Storage Temperature	All	-40 to +150	°C
T_{OPR}	Operating Temperature	All	-40 to +100	°C
T_{SOL}	Lead Solder Temperature	All	260 for 10 sec	°C
P_D	Total Device Power Dissipation @ T_A = 25°C	All	250	mW
	Derate above 25°C		2.94	mW/°C
EMITTER				
I_F	DC/Average Forward Input Current	All	60	mA
V_R	Reverse Input Voltage	TIL111M	3	V
		MOC8100M, TIL117M	6	
I_F(pk)	Forward Current – Peak (300µs, 2% Duty Cycle)	All	3	A
P_D	LED Power Dissipation @ T_A = 25 °C	All	120	mW
	Derate above 25°C		1.41	mW/°C
DETECTOR				
V_{CEO}	Collector-Emitter Voltage	All	30	V
V_{CBO}	Collector-Base Voltage	All	70	V
V_{ECO}	Emitter-Collector Voltage	TIL111M, TIL117M	7	V
V_{EBO}	Emitter-Base Voltage	All	7	
P_D	Detector Power Dissipation @ T_A = 25 °C	All	150	mW
	Derate above 25°C		1.76	mW/°C

Electrical Characteristics (T_A = 25°C unless otherwise specified.)

Individual Component Characteristics

Symbol	Parameter	Test Conditions		Device	Min.	Typ.*	Max.	Unit
EMITTER								
V_F	Input Forward Voltage	I_F = 16mA	T_A = 25°C	TIL111M		1.2	1.4	V
		I_F = 10mA for MOC8100M, I_F = 16mA; for TIL117M	T_A = 0°C–70°C	MOC8100M, TIL117M		1.2	1.4	
			T_A = -55°C			1.32		
			T_A = +100°C			1.10		
I_R	Reverse Leakage Current	V_R = 3.0V		TIL111M, TIL117M		0.001	10	µA
		V_R = 6.0V		MOC8100M		0.001	10	µA
DETECTOR								
BV_{CEO}	Collector-Emitter Breakdown Voltage	I_C = 1.0mA, I_F = 0		All	30	100		V
BV_{CBO}	Collector-Base Breakdown Voltage	I_C = 10µA, I_F = 0		All	70	120		V
BV_{EBO}	Emitter-Base Breakdown Voltage	I_E = 10µA, I_F = 0		All	7	10		V
BV_{ECO}	Emitter-Collector Breakdown Voltage	I_F = 100µA, I_F = 0		TIL111M, TIL117M	7	10		V
I_{CEO}	Collector-Emitter Dark Current	V_{CE} = 10V, I_F = 0		TIL111M, TIL117M		1	50	nA
		V_{CE} = 5V, T_A = 25°C		MOC8100M		0.5	25	nA
		V_{CE} = 30V, I_F = 0, T_A = 70°C		TIL117M, MOC8100M		0.2	50	µA
I_{CBO}	Collector-Base Dark Current	V_{CB} = 10V		TIL111M, TIL117M			20	nA
I_{CBO}		V_{CB} = 5V		MOC8100M			10	nA
C_{CE}	Capacitance	V_{CE} = 0V, f = 1MHz		All		8		pF

*All Typical values at T_A = 25°C

Electrical Characteristics (Continued) (T_A = 25°C unless otherwise specified.)

Transfer Characteristics

Symbol	Parameter	Test Conditions	Device	Min	Typ*	Max	Unit
DC CHARACTERISTICS							
CTR_{CE}	Current Transfer Ratio, Collector to Emitter	I_F = 10mA, V_{CE} = 10V	TIL117M	50			%
		I_F = 1mA, V_{CE} = 5V	MOC8100M	50			%
		I_F = 1mA, V_{CE} = 5V, T_A = 0°C to +70°C		30			
$I_{C(ON)}$	On-State Collector Current (Phototransistor Operation)	I_F = 16mA, V_{CE} = 0.4V	TIL111M	2			mA
	On-State Collector Current (Photodiode Operation)	I_F = 16mA, V_{CB} = 0.4V		7			µA
$V_{CE\ (SAT)}$	Collector-Emitter Saturation Voltage	I_C = 500µA, I_F = 10mA	TIL117M			0.4	V
		I_C = 2mA, I_F = 16mA	TIL111M			0.4	
		I_C = 100µA, I_F = 1mA	MOC8100M			0.5	
AC CHARACTERISTICS							
T_{ON}	Turn-On Time	I_C = 2mA, V_{CC} = 10V, R_L = 100Ω (Fig. 11)	MOC8100M			20	µs
			TIL117M			10	
T_{OFF}	Turn-Off Time		MOC8100M			20	µs
			TIL117M			10	
t_r	Rise Time		MOC8100M		2		µs
t_f	Fall Time		TIL117M		2		
t_r	Rise Time (Phototransistor Operation)	$I_{C(ON)}$ = 2mA, V_{CC} = 10V, R_L = 100Ω (Fig. 11)	TIL111M			10	µs
t_f	Fall Time (Phototransistor Operation)						

Isolation Characteristics

Symbol	Characteristic	Test Conditions	Min.	Typ.*	Max.	Units
V_{ISO}	Input-Output Isolation Voltage	f = 60Hz, t = 1 sec.	7500			$V_{AC(rms)}$
R_{ISO}	Isolation Resistance	V_{I-O} = 500 VDC	10^{11}			Ω
C_{ISO}	Isolation Capacitance	V_{I-O} = 0, f = 1MHz		0.2		pF

*All Typical values at T_A = 25°C

Safety and Insulation Ratings

As per IEC 60747-5-2, this optocoupler is suitable for “safe electrical insulation” only within the safety limit data. Compliance with the safety ratings shall be ensured by means of protective circuits.

Symbol	Parameter	Min.	Typ.	Max.	Unit
	Installation Classifications per DIN VDE 0110/1.89 Table 1				
	For Rated Main Voltage < 150Vrms		I-IV		
	For Rated Main voltage < 300Vrms		I-IV		
	Climatic Classification		55/100/21		
	Pollution Degree (DIN VDE 0110/1.89)		2		
CTI	Comparative Tracking Index	175			
V_{PR}	Input to Output Test Voltage, Method b, V_{IORM} x 1.875 = V_{PR}, 100% Production Test with tm = 1 sec, Partial Discharge < 5pC	1594			V_{peak}
	Input to Output Test Voltage, Method a, V_{IORM} x 1.5 = V_{PR}, Type and Sample Test with tm = 60 sec, Partial Discharge < 5pC	1275			V_{peak}
V_{IORM}	Max. Working Insulation Voltage	850			V_{peak}
V_{IOTM}	Highest Allowable Over Voltage	6000			V_{peak}
	External Creepage	7			mm
	External Clearance	7			mm
	Insulation Thickness	0.5			mm
RIO	Insulation Resistance at Ts, V_{IO} = 500V	10^9			Ω

Typical Performance Characteristics

Fig. 1 LED Forward Voltage vs. Forward Current

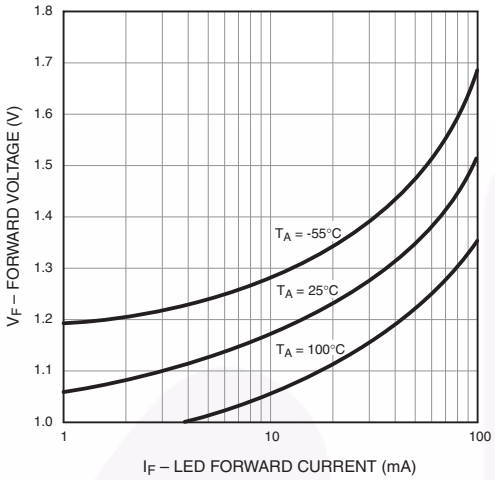


Fig. 2 Normalized CTR vs. Forward Current

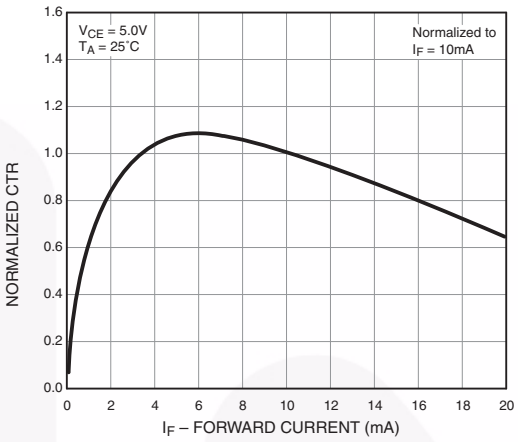


Fig. 3 Normalized CTR vs. Ambient Temperature

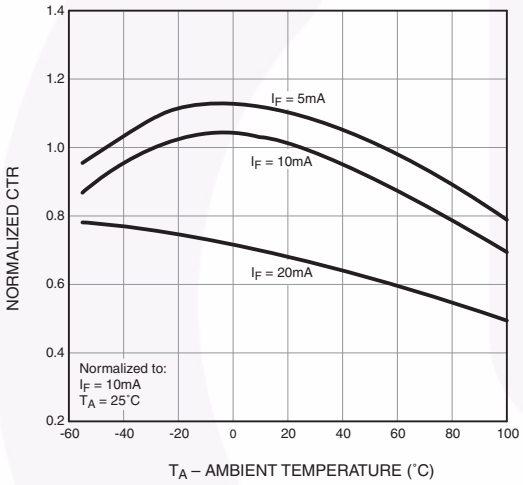


Fig. 4 CTR vs. RBE (Unsaturated)

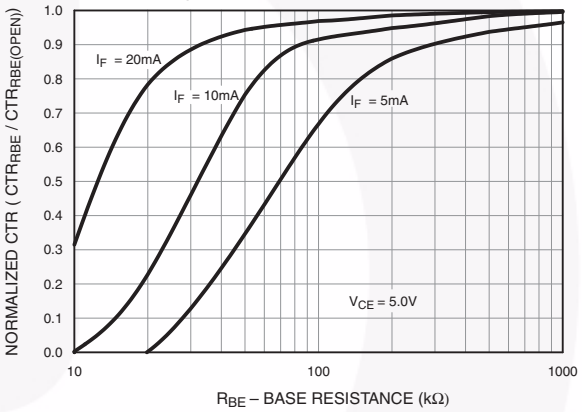


Fig. 5 CTR vs. RBE (Saturated)

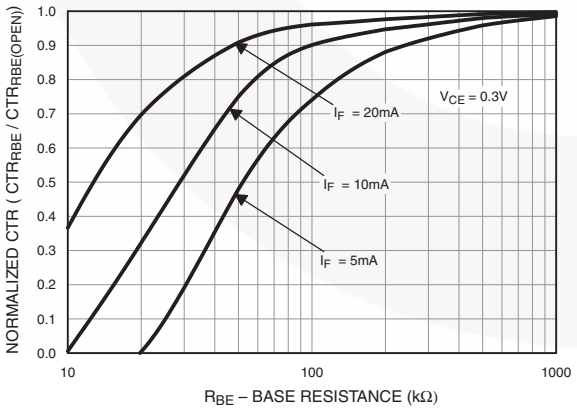
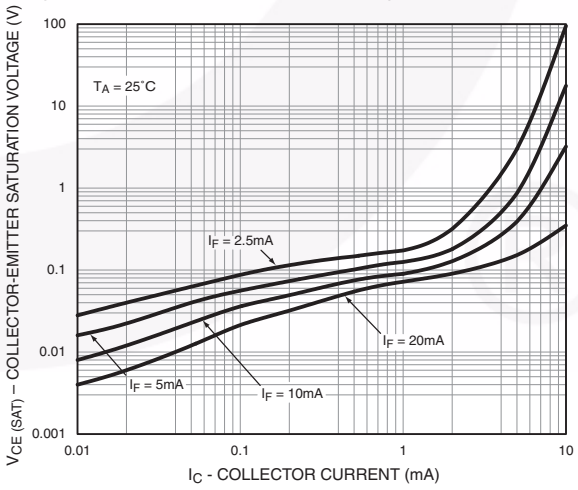


Fig. 6 Collector-Emitter Saturation Voltage vs Collector Current



Typical Performance Characteristics (Continued)

Fig. 7 Switching Speed vs. Load Resistor

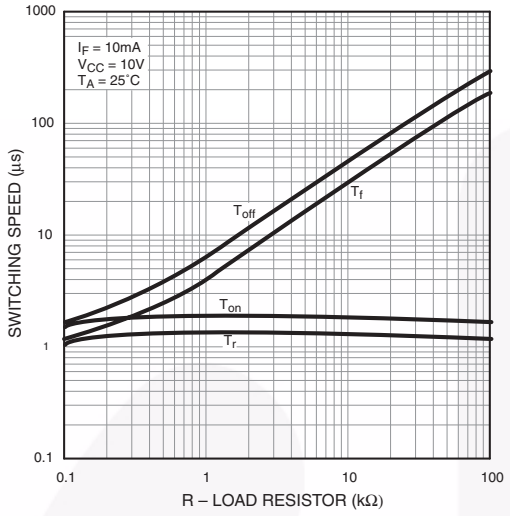


Fig. 8 Normalized t_{on} vs. R_{BE}

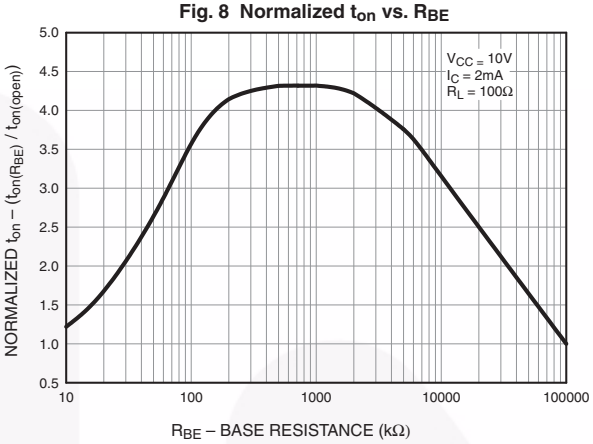


Fig. 9 Normalized t_{off} vs. R_{BE}

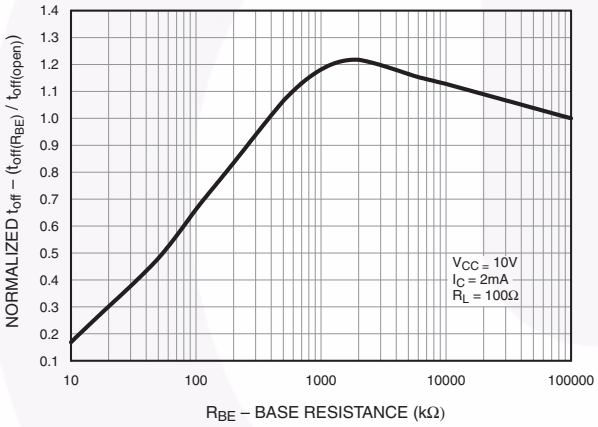
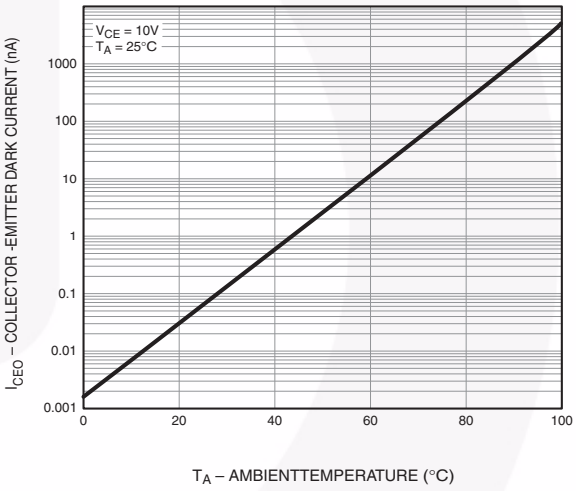
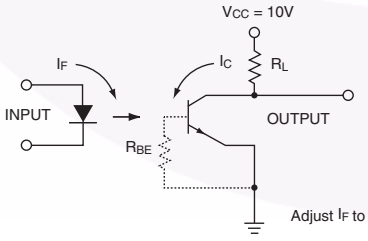


Fig. 10 Dark Current vs. Ambient Temperature



TEST CIRCUIT



WAVEFORMS

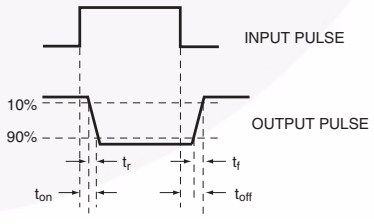
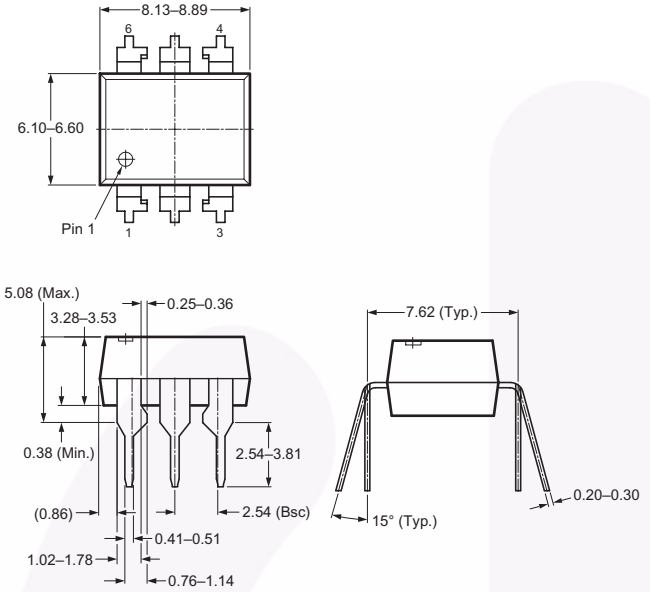


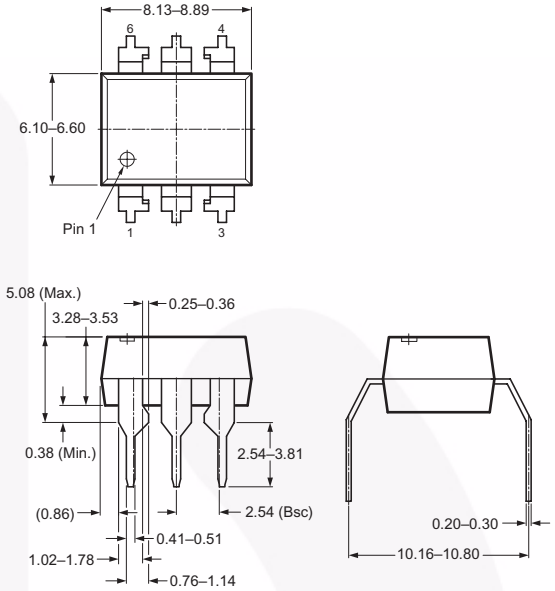
Figure 11. Switching Time Test Circuit and Waveforms

Package Dimensions

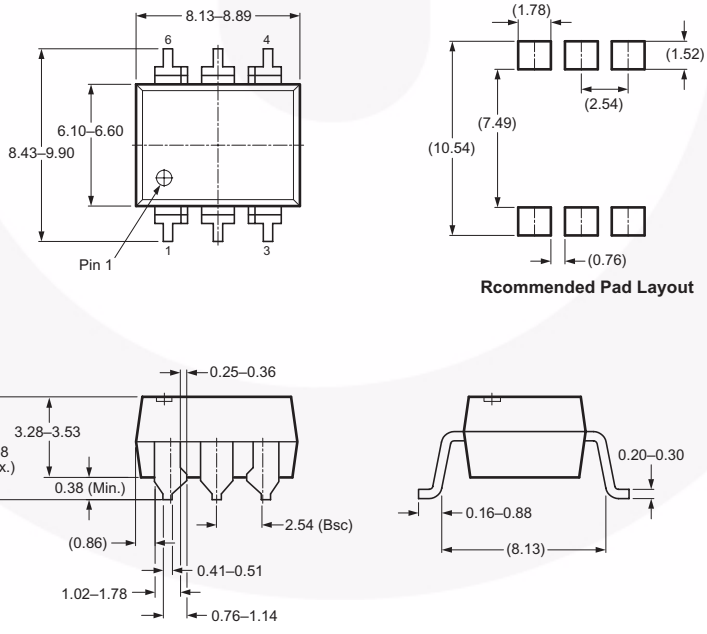
Through Hole



0.4" Lead Spacing



Surface Mount

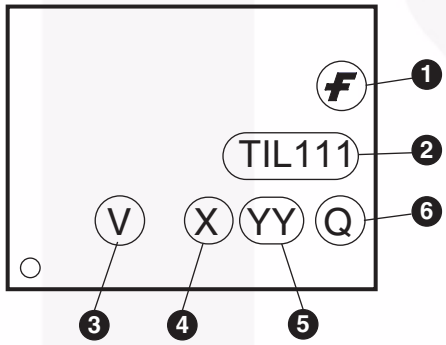


Note:
All dimensions in mm.

Ordering Information

Option	Order Entry Identifier (Example)	Description
No option	TIL111M	Standard Through Hole Device
S	TIL111SM	Surface Mount Lead Bend
SR2	TIL111SR2M	Surface Mount; Tape and Reel
T	TIL111TM	0.4" Lead Spacing
V	TIL111VM	VDE 0884
TV	TIL111TVM	VDE 0884, 0.4" Lead Spacing
SV	TIL111SVM	VDE 0884, Surface Mount
SR2V	TIL111SR2VM	VDE 0884, Surface Mount, Tape and Reel

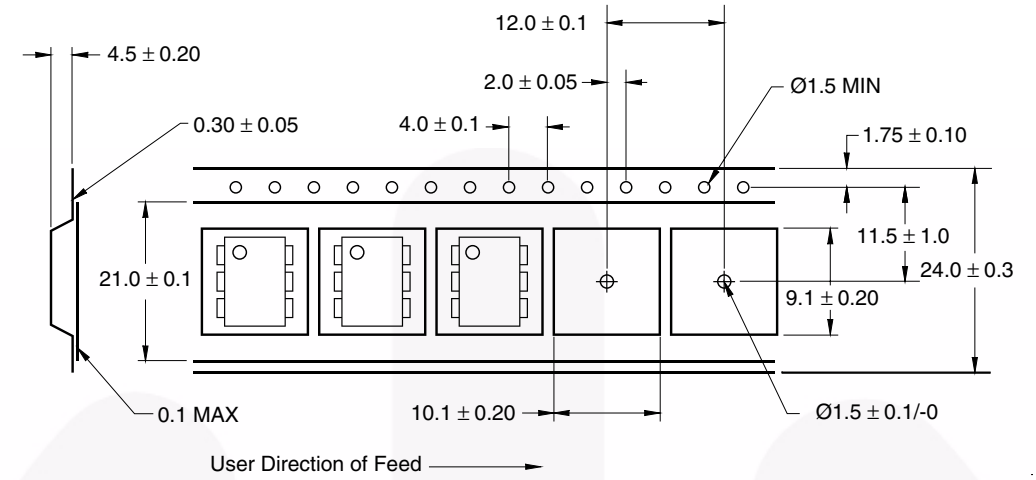
Marking Information



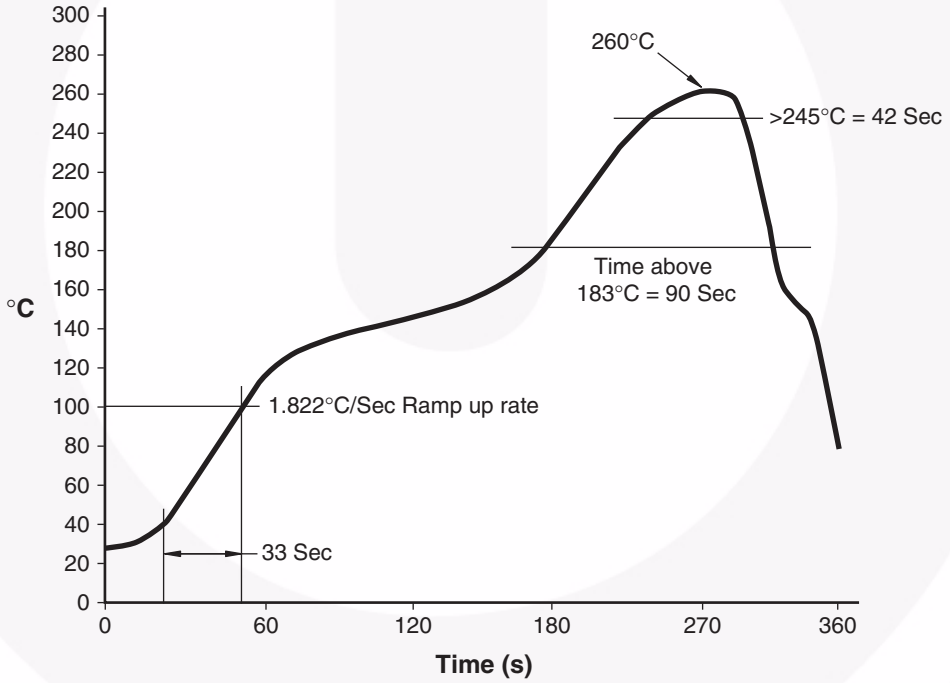
Definitions	
1	Fairchild logo
2	Device number
3	VDE mark (Note: Only appears on parts ordered with VDE option – See order entry table)
4	One digit year code, e.g., ‘7’
5	Two digit work week ranging from ‘01’ to ‘53’
6	Assembly package code

*Note – Parts that do not have the ‘V’ option (see definition 3 above) that are marked with date code ‘325’ or earlier are marked in portrait format.

Carrier Tape Specification



Reflow Profile



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Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

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